

Silicon NPN Power Transistors

2SC1469

DESCRIPTION

- With TO-3 package
- High breakdown voltage

APPLICATIONS

- For high voltage ,fast switching applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		10	A
I_B	Base current		4	A
P_T	Total power dissipation	$T_C \leq 25^\circ\text{C}$	100	W
T_j	Junction temperature		200	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	1.25	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=100mA$; $I_B=0$	400			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A$; $I_B=1A$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5A$; $I_B=1A$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=500V$; $I_E=0$			0.1	mA
I_{CEO}	Collector cut-off current	$V_{CE}=400V$; $I_B=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7V$; $I_C=0$			0.1	mA
h_{FE-1}	DC current gain	$I_C=1A$; $V_{CE}=5V$	15		50	
h_{FE-2}	DC current gain	$I_C=5A$; $V_{CE}=5V$	8			
f_T	Transition frequency	$I_C=1A$; $V_{CE}=5V$		10		MHz

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PACKAGE OUTLINE

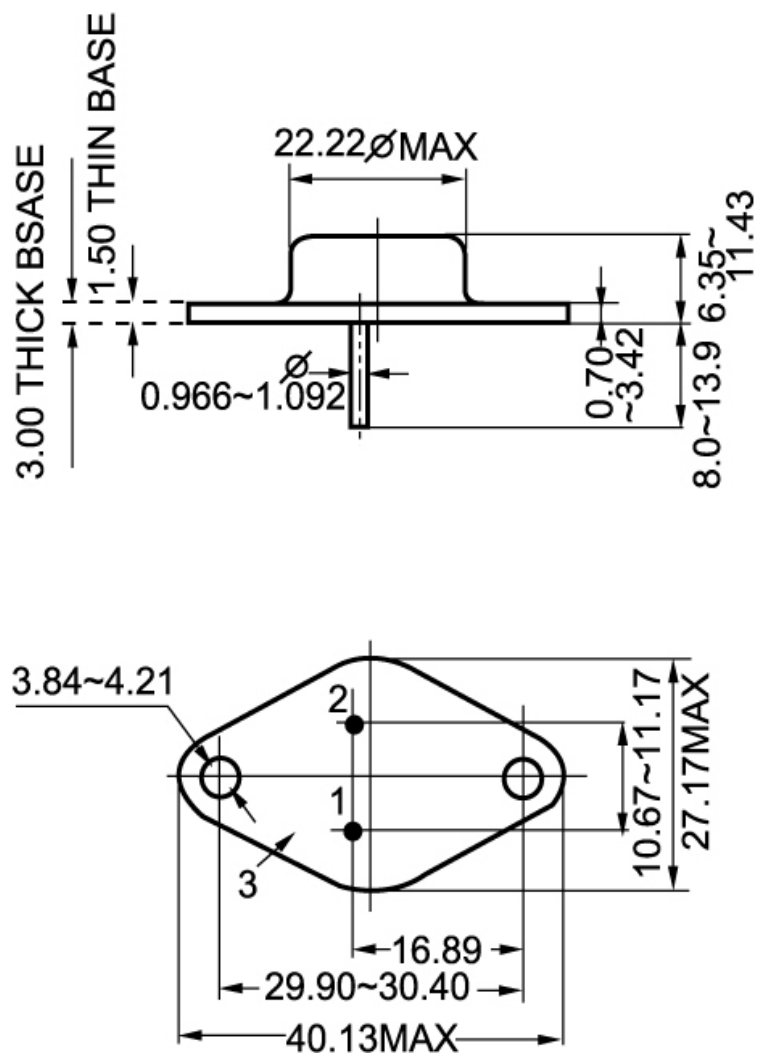


Fig.2 Outline dimensions